# Thyristor High Voltage, Phase Control SCR, 100 A



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### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I <sub>T(AV)</sub> 100 A								
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V							
V <sub>TM</sub> (typ.)	1.17 V							
I <sub>GT</sub>	100 mA							
TJ	-40 °C to +150 °C							
Package	TO-247AD 3L							
Circuit configuration	Single SCR							

### **FEATURES**

- qualified Designed and according to JEDEC<sup>®</sup>-JESD 47 RoHS
- 150 °C maximum operating junction temperature COMPLIANT
- HALOGEN • Material categorization: FREE for definitions of compliance please see www.vishay.com/doc?99912

### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

#### DESCRIPTION

The VS-100TPS12L high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

### **MECHANICAL DATA**

Case: TO-247AD 3L

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V				
On-state voltage	VT	100 A, T <sub>J</sub> = 125 °C, typical	1.17	v				
Average rectified forward current	I <sub>T(AV)</sub>		100					
Maximum continuous RMS on-state current	I <sub>RMS</sub>		157	А				
Non-repetitive peak surge current	I <sub>TSM</sub>	$T_J$ = 150 °C, 10 ms sine	935					
Maximum rate of rise	dV/dt		1000	V/µs				
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C				

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	TYP. I <sub>RRM</sub> ∕I <sub>DRM</sub> AT 150 °C mA					
VS-100TPS12L-M3	1200	1300	28					

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# VS-100TPS12L-M3



## Vishay Semiconductors

<b>ABSOLUTE MAXIMUM RATING</b>	S					
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS		MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$T_C$ = 103 °C, 180° conduction half sine	$T_C = 103 \text{ °C}$ , 180° conduction half sine wave		100	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			-	157	А
Peak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, rated $V_{\text{RRM}}$ applied		-	790	
Teak, one-cycle non-repetitive surge current	ISM	10 ms sine pulse, no voltage reapplied	Initial T <sub>J</sub> =	-	935	
I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{\mbox{\scriptsize RRM}}$ applied	T <sub>J</sub> maximum	-	3090	A <sup>2</sup> s
	1-1	10 ms sine pulse, no voltage reapplied		-	4370	A-2
$I^2\sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplie	ed, T <sub>J</sub> = 150 °C	-	43 700	A²√s
		100 A, T <sub>J</sub> = 25 °C		1.22	1.37	
On-state voltage	VT	190 A, T <sub>J</sub> = 25 °C		1.45	1.61	V
	v <sub>T</sub>	100 A, T <sub>J</sub> = 125 °C		1.17	1.26	, v
		190 A, T <sub>J</sub> = 125 °C		1.47	1.60	
Low level value of threshold voltage	V <sub>T01</sub>	T 150 %O		-	0.82	v
High level value of threshold voltage	V <sub>T02</sub>	T <sub>J</sub> = 150 °C		-	0.93	v
Low level value of on-state slope resistance	r <sub>t1</sub>	T 150.00		-	3.80	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	T <sub>J</sub> = 150 °C		-	3.50	11152
Rate of rise of turned-on current	dl/dt	$T_J$ = 150 °C, $V_R$ < 800 V, $I_T$ = 100 A, $I_{gt}$ : $t_r$ < 100 ns, repetitive	= 200 mA,	-	200	A/µs
Rate of rise of turned-on current	dl/dt	$T_J$ = 150 °C, $V_R$ < 1000 V, $I_T$ = 100 A, $I_{gi}$ $t_r$ < 100 ns, non repetitive	t = 200 mA,	-	500	A/µs
Holding current	Ι <sub>Η</sub>	Anada averative land T	AF %0	-	300	
Latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		-	500	mA
		T <sub>J</sub> = 25 °C		30	100	μA
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C		10	50	
		T <sub>J</sub> = 150 °C			70	mA
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V <sub>DRM</sub> ,	R <sub>a-k</sub> = open	-	1000	V/µs

TRIGGERING										
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS				
Peak gate power	P <sub>GM</sub>		no voltago reapplied	-	10	w				
Average gate power	P <sub>G(AV)</sub>	TO THS SILLE PUR	se, no voltage reapplied	-	2.5	~~				
Peak gate current	I <sub>GM</sub>			-	2.5	A				
Peak negative gate voltage	-V <sub>GM</sub>			-	10					
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	1.2	1.7					
Dequired DC gets veltage to trigger	N	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	1.0	1.5	V				
Required DC gate voltage to trigger	V <sub>GT</sub>	T <sub>J</sub> = 125 °C	Anode supply = 6 V resistive load	0.7	1.3					
		T <sub>J</sub> = 150 °C	Anode supply = 6 V resistive load	0.6	1.1					
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	80	150					
Dequired DC gets to trigger		T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	60	100					
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 125 °C	Anode supply = 6 V resistive load	25	50	mA				
		T <sub>J</sub> = 150 °C	Anode supply = 6 V resistive load	17	35					
DC gate voltage not to trigger	V <sub>GD</sub>			-	0.20	V				
DC gate current not to trigger	I <sub>GD</sub>	$I_{\rm J} = 150 {}^{\circ}\rm{C},  V_{\rm E}$	DRM = 80 % rated value	-	3.0	mA				

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t <sub>gt</sub>	$I_T$ = 100 A, $V_D$ = 50 % $V_{DRM},I_{gt}$ = 300 mA, $T_J$ = 25 °C	1.8	-	
Turn-off time	t <sub>q</sub>	$ I_T = 100 \text{ A}, V_D = 80 \ \% \ V_{DRM}, \ dV/dt = 20 \ V/\mu s, \ t_p = 200 \ \mu s \\ I_{gt} = 100 \ mA, \ dI/dt = 10 \ A/\mu s, \ V_R = 100 \ V, \ T_J = 150 \ ^\circ C $	135	-	μs

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DEVICE	S	INE HALF	NE HALF-WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION					UNITS			
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-100TPS12L-M3	0.032	0.047	0.042	0.044	0.046	0.030	0.039	0.041	0.044	0.046	°C/W

THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNITS			
Maximum operating junction and s	storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40	150	°C			
Maximum thermal resistance, junction to case		R <sub>thJC</sub>		-	0.25				
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		-	40	°C/W			
Typical thermal resistance, case to	o heatsink	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.	20				
Approximate weight				(	6	g			
Mounting torque	minimum			6	(5)	kgf · cm			
Mounting torque	e maximum			12	(10)	(lbf ⋅ in)			
Marking device			Case style TO-247AD 3L	1	100TPS	12L			

Maximum Average On-State Power Loss (W)

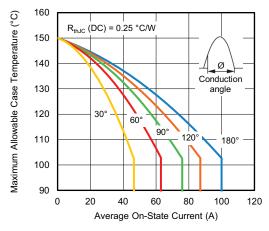


Fig. 1 - Current Rating Characteristics

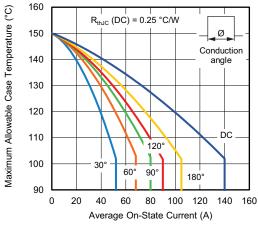


Fig. 2 - Current Rating Characteristics

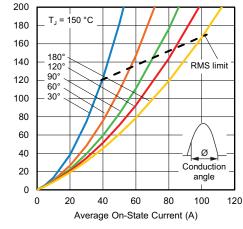


Fig. 3 - On-State Power Loss Characteristics

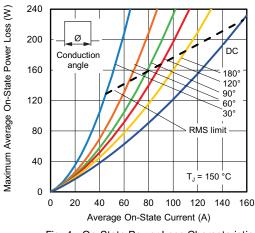


Fig. 4 - On-State Power Loss Characteristic

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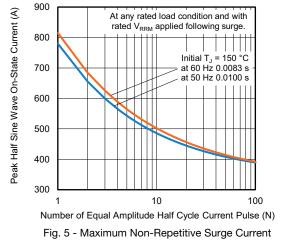
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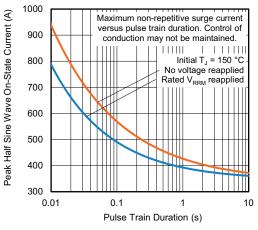
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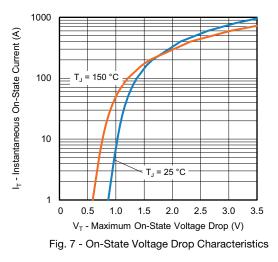
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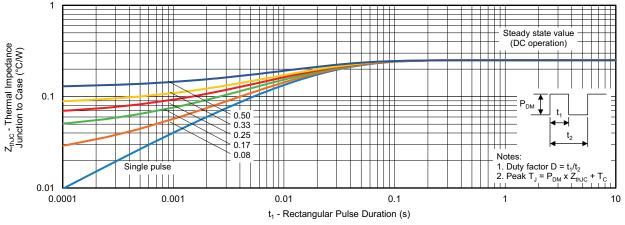
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### **ORDERING INFORMATION TABLE**

Device code	VS-	100	т	Р	S	12	L	-M3
	1	2	3	4	5	6	7	8
	<ol> <li>Vishay Semiconductors product</li> <li>Current code (100 = 100 A)</li> <li>Circuit configuration: T = thyristor</li> <li>P = TO-247 package</li> </ol>							
	5 - 6 - 7 - 8 -	S = Volt Pac	age coo kage L	d recove de (12 = = long le gen-free	1200 V ead	)	ant, and	termina

ORDERING INFORMATION (example)								
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-100TPS12L-M3	25	500	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				



TO-247AD 3L

### **DIMENSIONS** in millimeters and inches



View B

SYMBOL	MILLIN	MILLIMETERS		HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØК	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- <sup>(3)</sup> Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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